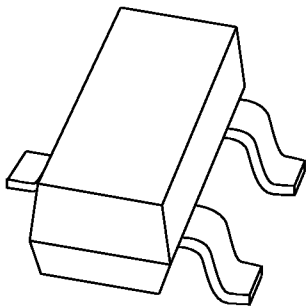


# DATA SHEET



## **BC859; BC860** PNP general purpose transistor

Product specification  
Supersedes data of 1997 May 26  
File under Discrete Semiconductors, SC10

1998 Jul 16

# PNP general purpose transistor

# BC859; BC860

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

### APPLICATIONS

- Low noise input stages of audio frequency equipment.

### DESCRIPTION

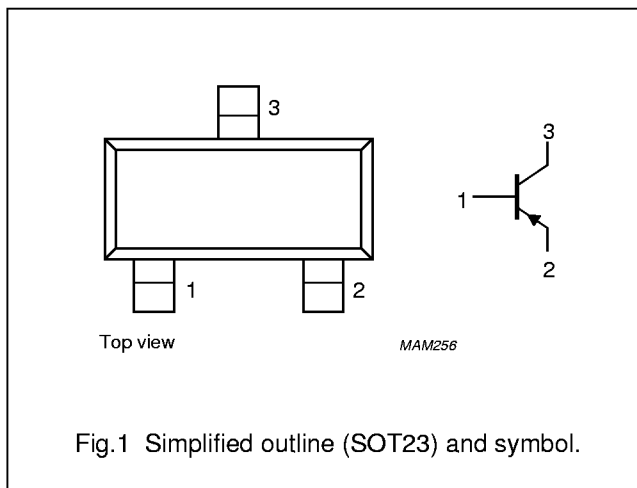
PNP transistor in a SOT23 plastic package.  
NPN complements: BC849 and BC850.

### MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BC859	4Dp	BC860	4Hp
BC859A	4Ap	BC860A	4Ep
BC859B	4Bp	BC860B	4Fp
BC859C	4Cp	BC860C	4Gp

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage BC859 BC860	open emitter	–	–30	V
			–	–50	V
V <sub>CEO</sub>	collector-emitter voltage BC859 BC860	open base	–	–30	V
			–	–45	V
I <sub>CM</sub>	peak collector current		–	–200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 60 °C	–	250	mW
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = –2 mA; V <sub>CE</sub> = –5 V	125	800	
f <sub>T</sub>	transition frequency	I <sub>C</sub> = –10 mA; V <sub>CE</sub> = –5 V; f = 100 MHz	100	–	MHz

## PNP general purpose transistor

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC859		–	–30	V
	BC860		–	–50	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC859		–	–30	V
	BC860		–	–45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–5	V
I <sub>C</sub>	collector current (DC)		–	–100	mA
I <sub>CM</sub>	peak collector current		–	–200	mA
I <sub>BM</sub>	peak base current		–	–200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

## PNP general purpose transistor

## BC859; BC860

**CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

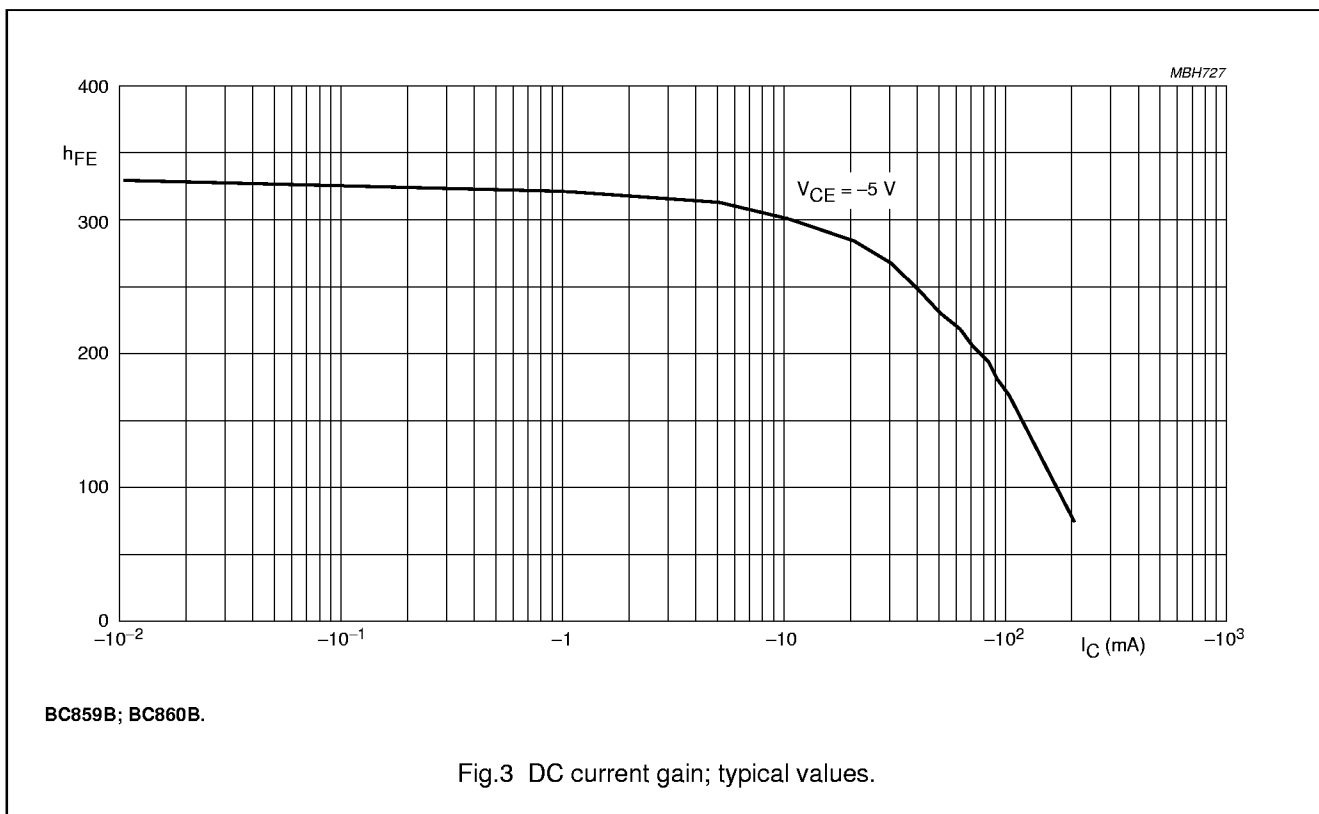
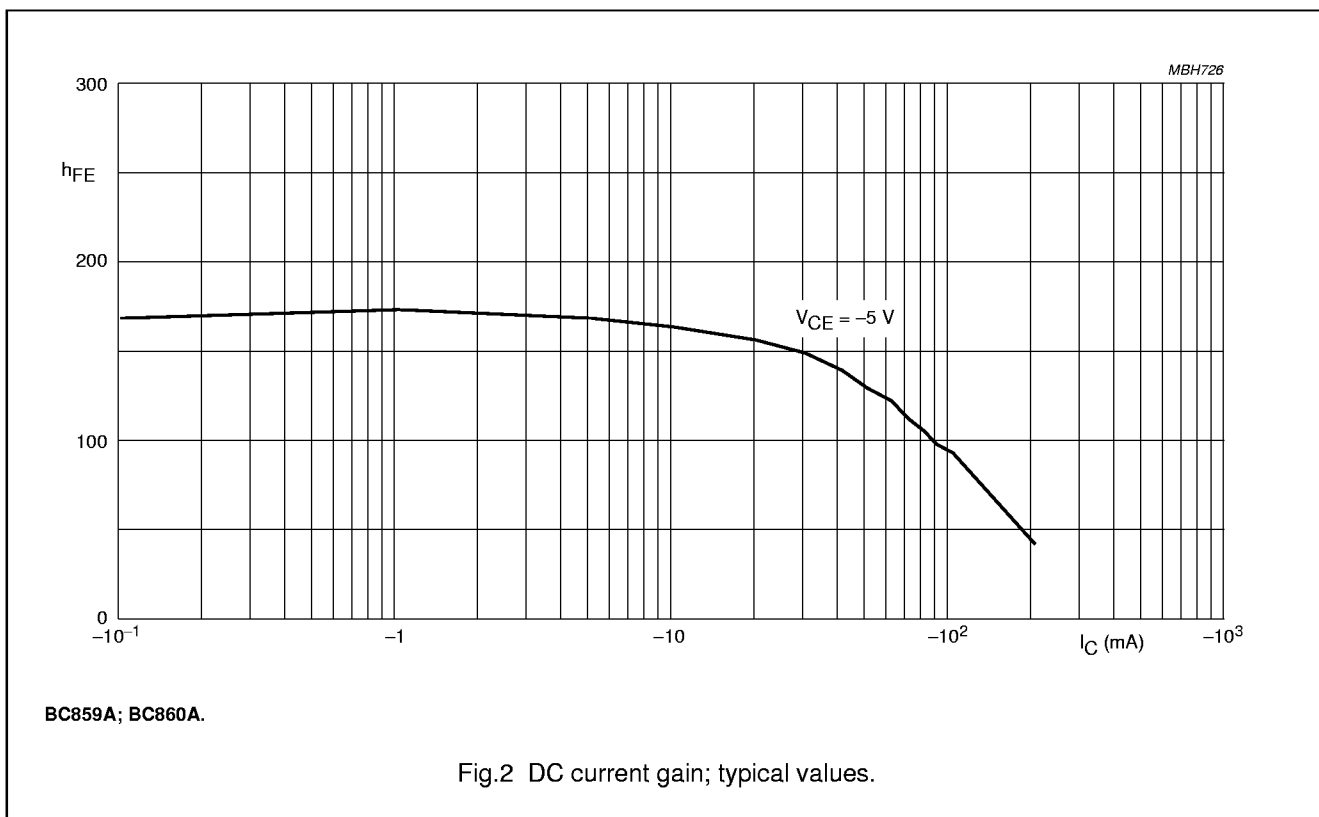
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–1	–15	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ °C}$	–	–	–4	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
$h_{FE}$	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	125	–	800	
$h_{FE}$	DC current gain BC859; BC860 BC859A; BC860A BC859B; BC860B BC859C; BC860C	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ see Figs 2, 3 and 4	125	–	800	
			125	–	250	
			220	–	475	
			420	–	800	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–75	–300	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA}$	–	–250	–650	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA};$ note 1	–	–700	–	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ note 1	–	–850	–	mV
$V_{BE}$	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–600	–650	–750	mV
		$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–	–	–820	mV
$C_c$	collector capacitance	$I_E = I_C = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	4.5	–	pF
$C_e$	emitter capacitance	$I_C = I_E = 0; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$	–	10	–	pF
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure BC859; BC860 BC859A; BC860A BC859B; BC860B BC859C; BC860C	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 30\text{ Hz to }15\text{ kHz}$	–	–	10	dB
			–	–	4	dB
			–	–	–	–
F	noise figure BC859; BC860 BC859A; BC860A BC859B; BC860B BC859C; BC860C	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB
			–	–	4	dB
			–	–	–	–

**Notes**

- $V_{BEsat}$  decreases by about  $-1.7\text{ mV/K}$  with increasing temperature.
- $V_{BE}$  decreases by about  $-2\text{ mV/K}$  with increasing temperature.

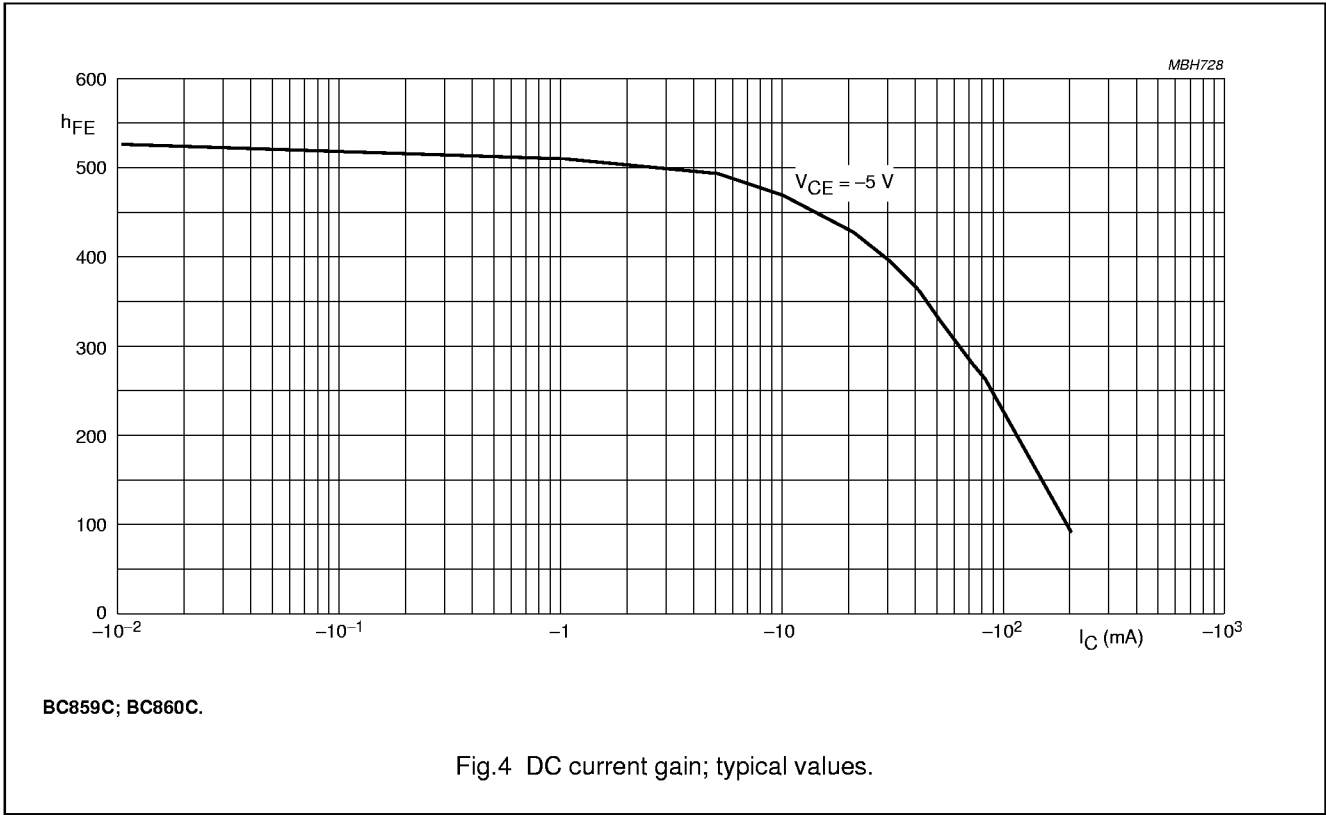
PNP general purpose transistor

BC859; BC860



PNP general purpose transistor

BC859; BC860



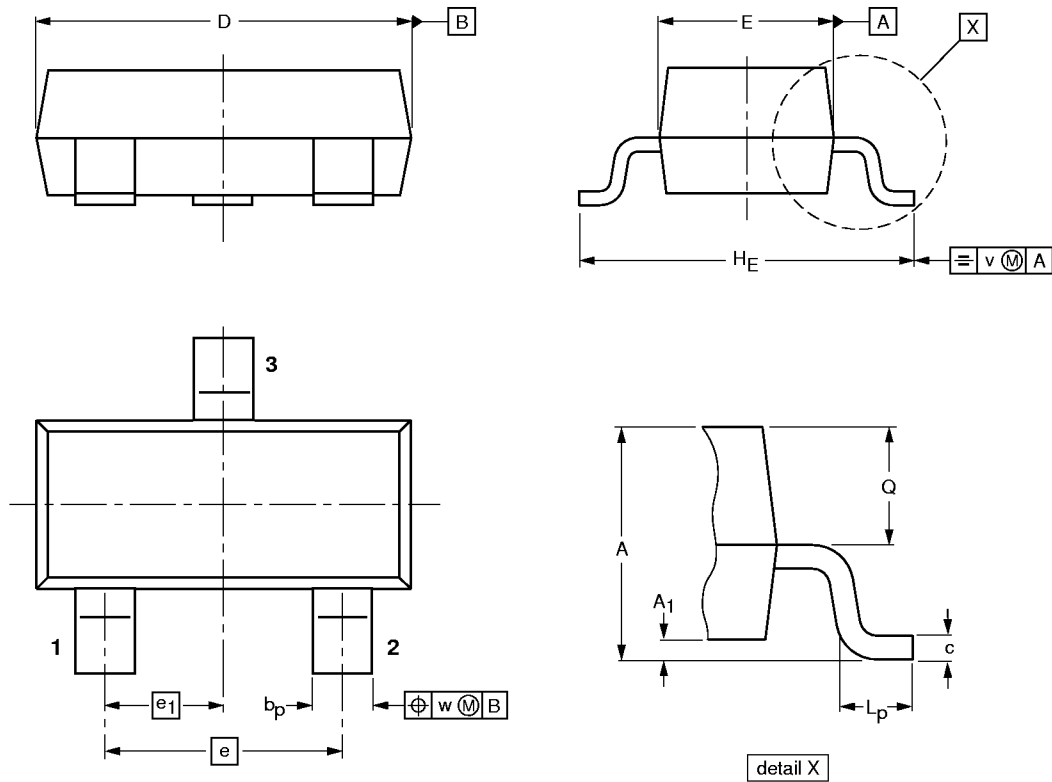
PNP general purpose transistor

BC859; BC860

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28